Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	50	self near3 limiting near3 (oxidizing oxidation oxidized oxidization) with oxide	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/01/25 06:35
L3	61	self near3 limiting near5 (oxidizing oxidation oxidized oxidization) with oxide	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/01/25 06:35
L4	66	self near3 limiting near6 (oxidizing oxidation oxidized oxidization) with oxide	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/01/25 06:35
L5	95	self near3 limiting with (oxidizing oxidation oxidized oxidization) with oxide	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/01/25 06:36
L6	95	self with limiting with (oxidizing oxidation oxidized oxidization) with oxide	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/01/25 06:36
S58	1	10/630969	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/01/24 17:16
S59	7144	oxide with low adj pressure	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/01/24 17:17
S60	476	S59 and (oxide low adj pressure) with torr	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/01/24 17:17
S61	478	S59 and (oxide low adj pressure) with (torr pascal)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/01/24 17:18
S62	479	S59 and (oxide low adj pressure) with (torr pascal atmosphereic)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/01/24 17:18

S63	370	S62 and (oxide with (thick thickness thicker))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/01/24 17:19
S64	146	S63 and ((oxide thick thickness thicker) with angstrom)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/01/24 17:20
S65	74	S64 and (oxide with (oxygen 'o2' oxygen adj containing))	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/01/24 17:24
S66	206	oxide with self adj limiting near3 oxid$4	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/01/24 17:55
S67	50	oxide with self adj limiting near3 (oxidizing oxidation oxidized oxidization)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/01/24 17:56
S68	163	self adj limiting near3 (oxidizing oxidation oxidized oxidization)	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/01/24 17:57
S69	50	self adj limiting near3 (oxidizing oxidation oxidized oxidization) with oxide	US-PGPUB; USPAT; EPO; JPO	OR	ON	2006/01/25 06:35

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  - S58: (1) 10/630969
  - S59: (7144) oxide with low adj pres:

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DBs: US-PGPUB; USPAT; EPO; JPO

Default operator: OR

Plurals

Highlight all hit terms initially

self adj limiting near3 (oxidizing oxidation oxidized oxidization) with oxide

BRS form | ISR form | Image | Text | HTML

	U	1	Document ID	Issue Dat	Page	Title	Current O	Current X	Retrieva
1	☐	☐	US 20050059259 A	2005031	18	Interfacial oxidation process for high-k gate dielectric proce	438/765	257/E21.2	
2	☐	☐	US 20050026459 A	2005020	16	Method of forming uniform ultra-thin oxynitride layers	438/786	257/E21.2	
3	☐	☐	US 20050026453 A	2005020	15	Formation of ultra-thin oxide layers by self-limiting interfac	438/778	257/E21.2	
4	☐	☐	US 20040229447 A	2004111	26	Process for producing luminescent silicon nanoparticles	438/507		
5	☐	☐	US 20040182915 A	2004092	16	Structure and method for bonding to copper interconnect st	228/220	228/215;	
6	☐	☐	US 20040087079 A	2004050	6	METHOD OF FORMING A NITRIDE GATE DIELECTRI	438/216	257/E21.1	
7	☐	☐	US 20030180556 A	2003092	5	Corrosive-resistant coating over aluminum substrates for us	428/472.2	427/255.28	
8	☐	☐	US 20030060057 A	2003032	10	Method of forming ultrathin oxide layer	438/770	257/E21.1	
9	☐	☐	US 20030052358 A	2003032	12	Method of improved high K dielectric - polysilicon interfac	257/310	257/309;	
10	☐	☐	US 20030049942 A	2003031	9	Low temperature gate stack	438/778	257/E21.1	
11	☐	☐	US 20030042526 A	2003030	12	Method of improved high K dielectric-polysilicon interface	257/309	257/E21.0	
12	☐	☐	US 20030032304 A	2003021	14	Process for the electrochemical oxidation of a semiconduct	438/770	257/E21.2	
13	☐	☐	US 20010031562 A	2001101	10	Method of forming ultrathin oxide layer	438/770	257/E21.1	
14	☐	☐	US 20010017421 A	2001083	3	Semiconductor element with metal layer	257/767	257/E21.5	
15	☐	☐	US 6974779 B2	2005121	17	Interfacial oxidation process for high-k gate dielectric proce	438/769	438/770	
16	☐	☐	US 6863926 B2	2005030	5	Corrosive-resistant coating over aluminum substrates for us	427/250	427/249.15	
17	☐	☐	US 6806145 B2	2004101	11	Low temperature method of forming a gate stack with a hig	438/287	257/E21.1	
18	☐	☐	US 6794314 B2	2004092	11	Method of forming ultrathin oxide layer	438/778	257/E21.1	
19	☐	☐	US 6727134 B1	2004042	6	Method of forming a nitride gate dielectric layer for advanc	438/216	257/E21.1	
20	☐	☐	US 6550060 B2	2003050	13	Process for the electrochemical oxidation of a semiconduct	438/770	257/E21.2	

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File View Edit Tools Window Help

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  - S58: (1) 10/630969
  - S59: (7144) oxide with low adj pres

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DBs: US-PGPUB; USPAT; EPO; JPO

Default operator: OR

Plurals

Highlight all hit terms initially

self adj limiting near3 (oxidizing oxidation oxidized oxidization) with oxide

BRS form | IS&R form | Image | Text | HTML

	U	1	Document ID	Issue Dat	Page	Title	Current O	Current X	Retrieva
20	☐	☐	US 6559069 B2	2003050	13	Process for the electrochemical oxidation of a semiconduct	438/770	257/E21.2	
21	☐	☐	US 6492283 B2	2002121	11	Method of forming ultrathin oxide layer	438/770	257/E21.1	
22	☐	☐	US 6444592 B1	2002090	6	Interfacial oxidation process for high-k gate dielectric proce	438/770	257/E21.2	
23	☐	☐	US 6417564 B2	2002070	3	Semiconductor element with metal layer	257/740	257/763;	
24	☐	☐	US 6329722 B1	2001121	7	Bonding pads for integrated circuits having copper intercon	257/786	257/690;	
25	☐	☐	US 6197641 B1	2001030	17	Process for fabricating vertical transistors	438/268	257/E21.4	
26	☐	☐	US 6165914 A	2000122	5	Method for fabricating semiconductor devices with thick hi	438/787	257/E21.2	
27	☐	☐	US 6144071 A	2000110	18	Ultrathin silicon nitride containing sidewall spacers for imp	257/344	257/384;	
28	☐	☐	US 6103595 A	2000081	6	Assisted local oxidation of silicon	438/431	257/E21.5	
29	☐	☐	US 6063665 A	2000051	6	Method for silicon surface control for shallow junction for	438/260	257/E21.3	
30	☐	☐	US 5961791 A	1999100	11	Process for fabricating a semiconductor device	204/192.1	204/192.15	
31	☐	☐	US 5916378 A	1999062	10	Method of reducing metal contamination during semicondu	148/243	148/275;	
32	☐	☐	US 5804910 A	1998090	7	Field emission displays with low function emitters and met	313/310		
33	☐	☐	US 5661073 A	1997082	6	Method for forming field oxide having uniform thickness	438/431	257/E21.5	
34	☐	☐	US 5589422 A	1996123	16	Controlled, gas phase process for removal of trace metal co	438/476	134/1.3;	
35	☐	☐	US 5359216 A	1994102	9	DRAM process with improved polysilicon-to-polysilicon c	257/306	257/297;	
36	☐	☐	US 5334281 A	1994080	7	Method of forming thin silicon mesas having uniform thick	438/404	148/DIG.5	
37	☐	☐	US RE34535 E	1994020	9	Floating gate memory with improved dielectric	365/185.0	257/319;	
38	☐	☐	US 5244825 A	1993091	8	DRAM process with improved poly-to-poly capacitor	438/241	257/E27.0	
39	☐	☐	US 5104810 A	1992041	13	Fabrication of internally dielectric for EPROM related techn	438/593	257/E21.2	

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File View Edit Tools Window Help

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  - S58: (1) 10/630969
  - S59: (7144) oxide with low adj pres:

Search | Edit | Browse | Queue | Clear

OR | US-PGPUB; USPAT; EPO; JPO | Plurals | Highlight all hit terms initially

Default operator: OR

self adj limiting near3 (oxidizing oxidation oxidized oxidization) with oxide

BRS form | IS&R form | Image | Text | HTML

	U	1	Document ID	Issue Dat	Page	Title	Current O	Current X	Retrieva
32	☐	☐	US 5804910 A	1998090	7	Field emission displays with low function emitters and met	313/310		
33	☐	☐	US 5661073 A	1997082	6	Method for forming field oxide having uniform thickness	438/431	257/E21.5	
34	☐	☐	US 5589422 A	1996123	16	Controlled, gas phase process for removal of trace metal co	438/476	134/1.3;	
35	☐	☐	US 5359216 A	1994102	9	DRAM process with improved polysilicon-to-polysilicon c	257/306	257/297;	
36	☐	☐	US 5334281 A	1994080	7	Method of forming thin silicon mesas having uniform thick	438/404	148/DIG.5	
37	☐	☐	US RE34535 E	1994020	9	Floating gate memory with improved dielectric	365/185.0	257/319;	
38	☐	☐	US 5244825 A	1993091	8	DRAM process with improved poly-to-poly capacitor	438/241	257/E27.0	
39	☐	☐	US 5104819 A	1992041	13	Fabrication of interpoly dielctric for EPROM-related techn	438/593	257/E21.2	
40	☐	☐	US 5098192 A	1992032	10	DRAM with improved poly-to-poly capacitor	257/306	257/760;	
41	☐	☐	US 4949154 A	1990081	11	Thin dielectrics over polysilicon	257/311	257/371;	
42	☐	☐	US 4922312 A	1990050	8	DRAM process with improved polysilicon-to-polysilicon c	257/297	257/300;	
43	☐	☐	US 4697330 A	1987100	10	Floating gate memory process with improved dielectric	438/261	257/E21.6	
44	☐	☐	US 4656729 A	1987041	11	Dual electron injection structure and process with self-limit	438/261	257/316;	
45	☐	☐	US 4613956 A	1986092	8	Floating gate memory with improved dielectric	365/185.0	257/315;	
46	☑	☐	US 4577390 A	1986032	11	Fabrication of polysilicon to polysilicon capacitors with a c	438/396	257/371;	
47	☑	☐	US 4405659 A	1983092	9	Method for producing columnar grain ceramic thermal barri	427/248.1	427/250;	
48	☑	☐	US 4401697 A	1983083	10	Method for producing columnar grain ceramic thermal barri	427/250	204/192.15	
49	☑	☐	US 4321311 A	1982032	9	Columnar grain ceramic thermal barrier coatings	428/623	428/629;	
50	☑	☐	WO 2005013348 A	2005021		FORMATION OF ULTRA-THIN OXIDE AND OXYNITRI		257/E21.2	

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